

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Previously Presented) A semiconductor device comprising:  
a plurality of first bump electrodes arranged on a main surface, and each of said plurality of first bump electrodes receiving signals or power;  
a plurality of dummy bump electrodes arranged on said main surface, and each of said plurality of dummy bump electrodes electrically connected to an associated one of said plurality of first bump electrodes wherein said plurality of dummy bump electrodes and said plurality of first bump electrodes being arranged alternately along to circumference of bump group.
2. (Previously Presented) The semiconductor device as claimed in claim 1 further comprising:  
a plurality of protection circuits electrically coupled to said plurality of first bump electrodes.
3. (Original) The semiconductor device as claimed in claim 1, further comprising:  
a plurality of test electrodes electrically connected to said first bump electrodes.
4. (Original) The semiconductor device as claimed in claim 3, wherein  
said plurality of test electrodes being arranged along four edges of said semiconductor device.
5. (Previously Presented) The semiconductor device as claimed in claim 1, wherein  
said plurality of dummy bump electrodes being higher than a plurality of chip electrodes.
6. (Original) The semiconductor device as claimed in claim 1, wherein said plurality of dummy bump electrodes being arranged closer than said plurality of first bump electrodes.

7. (Previously Presented) The semiconductor device as claimed in claim 1, wherein said plurality of dummy bump electrodes being arranged between said plurality of first bump electrodes and a plurality of chip electrodes.

8. (Original) The semiconductor device as claimed in claim 1, wherein said plurality of dummy bump electrodes being provided for relaxation of stress at mounting said semiconductor device.

9.-18. (Canceled).

19. (Previously Presented) A semiconductor device comprising:  
a pad formed above a semiconductor chip;  
an external bump electrode formed above said semiconductor chip corresponding to said pad;  
a dummy bump electrode formed above said semiconductor chip ;  
a first wiring connected between said external bump electrode and said dummy bump electrode; and  
a second wiring connected between a center of said first wiring or a portion near to said external bump electrode from said center of said first wiring and said pad.

20. (Previously Presented) The semiconductor device as claimed in claim 22, wherein said dummy bump electrode is arranged in a direction along a side of said semiconductor chip.

21. (Previously Presented) The semiconductor device as claimed in claim 22, wherein said external bump electrode is arranged internally from a side of said semiconductor chip relative to said dummy bump electrode.

22. (Previously Presented) The semiconductor device as claimed in claim 19, wherein said dummy bump electrode is formed between said external bump electrode and said pad.

23. (Previously Presented) The semiconductor device as claimed in claim 19, wherein said external bump electrode receives a signal through said pad.

24. (Canceled).

25. (Currently Amended) ~~The semiconductor device as claimed in claim 24, A~~  
semiconductor device comprising:

a semiconductor chip;

a first pad formed above said semiconductor chip;

a second pad formed above said semiconductor chip;

a first external bump electrode above said semiconductor, and connected to said first  
pad;

a second external bump electrode above said semiconductor, and connected to said  
second pad;

a first dummy bump electrode above said semiconductor, and connected to said first  
external bump electrode; and

a second dummy bump electrode above said semiconductor, and connected to said  
second external bump electrode,

wherein said first dummy bump electrode is formed between said first pad and said first external bump electrode, and said second dummy bump electrode is formed between said second pad and said second external bump electrode.

26. (Canceled).